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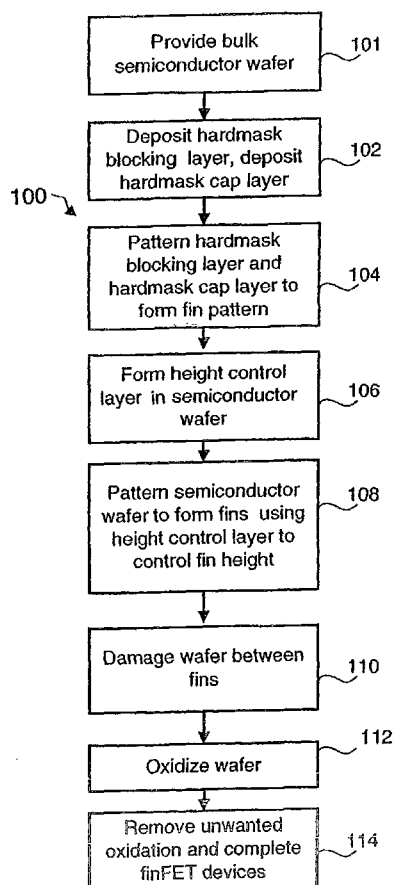
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(54) Title: FIN FET DEVICES FROM BULK SEMICONDUCTOR AND METHOD FOR FORMING



(57) Abstract: The present invention thus provides a device structure and method for forming fin (210) Field Effect Transistors (FETs) from bulk semiconductor wafers (200) while providing improved wafer to wafer device uniformity. Specifically, the invention provides a height control layer (212), such as a damaged portion of the substrate (200) or a marker layer, which provides uniformity of fin height. Additionally, the invention provides isolation (214) between fins (210) which also provides for optimization and narrowing of fin width by selective oxidation of a portion (212) of the substrate relative to an oxidized portion (216) of the fin sidewalk. The device structure and methods of the present invention thus provide the advantages of uniform finFET fabrication while using cost effect bulk wafers.



ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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